HG Semiconductors

HG RF POWER TRANSISTOR

MRF464

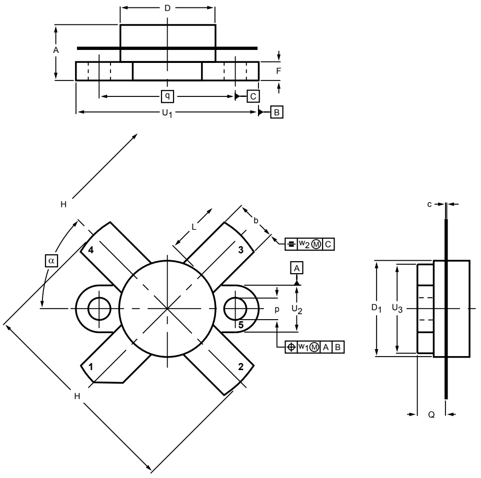
ROHS Compliance,Silicon NPN POWER TRANSISTOR

DESCRIPTION

Designed primarily for 28 –voltage applications as a high–power linear amplifier from 2.0 to 30 MHz.

FEATURES

- Specified 28V, 30MHz Characteristics
- P_O = 80W
- G_P = 15 dB min. at 80 W/28 MHz
- Omnigold™ Metalization System



1.Collector
2.EMITTER
3.BASE
4.EMITTER
5.FIN

DIMENSIONS

NOTE: ALL ELECTRODES ARE ISOLATED FROM FLANCE.

UNIT	A	b	c	D	D_1	F	H	L	p	Q	q	U_1	U_2	U_3	w_1	w_2	α
mm	7.27 6.17	5.82 5.56	0.16 0.10	12.86 12.59	12.83 12.57	2.67 2.41	28.45 25.52	7.93 6.32	3.30 3.05	4.45 3.91	18.42	24.90 24.63	6.48 6.22	12.32 12.06	0.51	1.02	45°
inches	0.286 0.243	0.229 0.219	0.006 0.004	0.506 0.496	0.505 0.495	0.105 0.095	1.120 1.005	0.312 0.249	0.130 0.120	0.175 0.154	0.725	0.98 0.97	0.255 0.245	0.485 0.475	0.02	0.04	

MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Collector-Base Voltage	V_{CBO}	65	V
Collector-Emitter Voltage	V_{CES}	65	V
Collector-Emitter Voltage	V_{CEO}	35	V
Collector Current	I_C	10	A
Emitter-Base Voltage	V_{EBO}	4	V
Collector Power Dissipation	P_{DISS}	250	W
Junction Temperature	T_J	-65 to 200	°C
Storage Temperature Range	T_{STG}	-65 to 175	°C

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP	MAX	UNITS
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=100mA,I_B=0	35	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	I_C=100mA,V_{EB}=0	65	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=10mA,I_C=0	4	-	-	V
Collector Cutoff Current	I_{CBO}	(V_{CB} = 30 V, I_E = 0)	-	-	5	mA
DC Current Gain	h_{FE}	V_{CE}=5V,I_C=2A	10	-	200	
Collector Output Capacitance	C_{Ob}	V_{CB}=28V,I_E=0 f=1MHz	-	-	200	pF
Power Gain	G_P	V_{CC}=28V,P_{OUT}=80W, f=30MHz	15.0	-	-	dB
Collector Efficiency	η_C		40	-		%

Note : Above parameters , ratings , limits and conditions are subject to change.

Sep. 1998